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Application Number

09/535.015

Filing Date

March 24, 2000

First Named Inventor

Shunpei YAMAZAKI et al.

Group Art Unit

2811

Examiner Name

S. Crane

Sheet 1 of 1 Attorney Docket Number

U.S. PATENT DOCUMENTS

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Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SC		NEMANICH, R.J. et al., <i>Structure and Growth of the Interface of Pd on a-SiH</i> , The America Physical Society - Physical Review, Vol. 23, No. 12, Pages 6828-6831, June 1981.	

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>Use as many sheets as necessary)</small>			Application Number	09/535,015
			Filing Date	March 24, 2000
			First Named Inventor	Shunpei YAMAZAKI et al.
			Group Art Unit	2811
			Examiner Name	S. Crane
			Attorney Docket Number	0756-2131
Sheet	1	of	1	

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		NEMANICH, R.J. et al. Structure and Growth of the Interface of Pd on a-Si:H, The America Physical Society - Physical Review, Vol. 23, No. 12, Pages 6828-6831, June 1981. see I.D.S. of May 02 2006	

Examiner Signature	/Sara Crane/	Date Considered	05/12/2006
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Form P-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 0756-2131		Serial No. Not Yet Assigned	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant: Shunpei YAMAZAKI et al.				U.S. Patent Office 06/15/2001	
		Filing Date: March 24, 2000		Group: 2811			
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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)	
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SWL	R.J. Nemanich et al, "Structure and Growth of the Interface of Pd on α -Si:H", The American Physical Society - Physical Review, Vol. 22, No. 12, pp. 6828-6834, June 1981						
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